

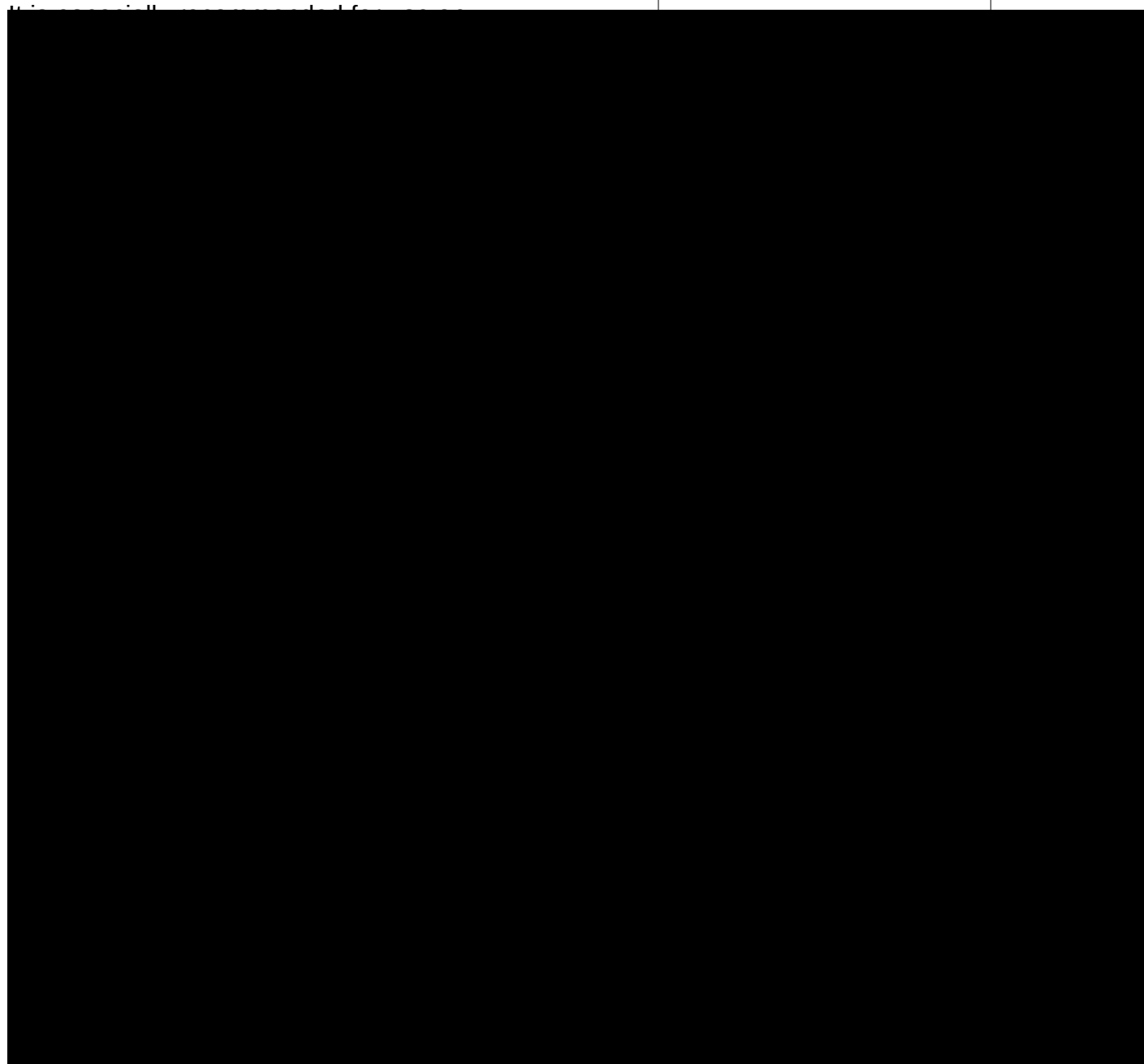


JCT616E 16A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT616E of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.



Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	dI/dt	150	A/s
Peak gate current (t_p)			

Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33$	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3k$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	60	mA
I_H	$I_T=500mA$	-	-	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125^\circ\text{C}$	1200	-	-	V/s
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ\text{C}$	-	4	-	s
t_{off}		-	60	-	

STATIC CHARACTERISTICS

Symbol

JCT616E

J

JCT616E

JCT616E

J

Technical drawing of a rectangular block with dimensions A, B, C, D, E, F, and G. The drawing shows a perspective view of the block with a rectangular cutout on the front face. The dimensions are labeled as follows: A is the width of the block, B is the height of the block, C is the height of the front face, D is the width of the cutout, E is the depth of the cutout, F is the width of the cutout, and G is the height of the cutout.



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033

DELIVERY MODE

